



80V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
80V	$17m\Omega @ V_{GS} = 10V$	65A
00 V	$21m\Omega$ @ $V_{GS} = 4.5V$	59A

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

PowerDI5060-8

- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

Features

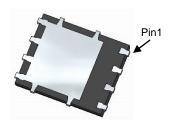
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

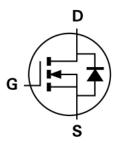
- Case: PowerDI[®] 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



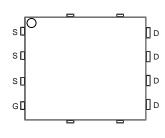




Bottom View



Internal Schematic



Top View Pin Configuration

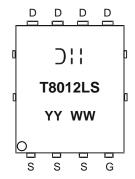
Ordering Information (Note 4)

-			
	Part Number	Case	Packaging
	DMT8012LPS-13	PowerDI5060-8	2.500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



T8012LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)

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Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	80	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	9 7.2	А
Continuous Drain Current, $V_{GS} = 10V$ (Note 6) $T_C = +25^{\circ}C$ $T_C = +70^{\circ}C$		I _D	65 51	А
Maximum Continuous Body Diode Forward Current (Note 6)		Is	80	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	80	Α
Avalanche Current, L=0.1mH		I _{AS}	11.6	Α
Avalanche Energy, L=0.1mH		E _{AS}	10.2	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	56	°C/W
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		P_{D}	113	W
Thermal Resistance, Junction to Case (Note 6)		R ₀ JC	1.1	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	80	-	=	٧	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	V _{DS} = 64V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	1	1.3	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Pages	-	14	17	mΩ	$V_{GS} = 10V, I_D = 12A$	
Static Brain-Source On-Nesistance	R _{DS(ON)}	-	16.5	21	11152	$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V_{SD}	-	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	1,949	-		101/1/	
Output Capacitance	Coss	-	177	-	pF	$V_{DS} = 40V$, $V_{GS} = 0V$, f = 1MHz	
Reverse Transfer Capacitance	C_{rss}	-	10	-			
Gate Resistance	R_g	-	0.7	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	15	-			
Total Gate Charge (V _{GS} = 10V)	Q_g	-	34	-	nC	Vps = 40V. lp = 12A	
Gate-Source Charge	Q_gs	-	6	-	110	V _{DS} = 40V, I _D = 12A	
Gate-Drain Charge	Q_{gd}	-	4.5	-			
Turn-On Delay Time	t _{D(ON)}	-	4.9	-			
Turn-On Rise Time	t _R	-	3.8	-	ns	$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 12A, R_{G} = 1.6\Omega$	
Turn-Off Delay Time	t _{D(OFF)}	-	16.5	-	ns		
Turn-Off Fall Time	t _F	-	3.5	-			
Body Diode Reverse Recovery Time	t _{RR}	-	30.2	-	ns	I_ 124 di/dt 1004/va	
Body Diode Reverse Recovery Charge	Q_{RR}	-	34.6	-	nC	I _F = 12A, di/dt = 100A/μs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.



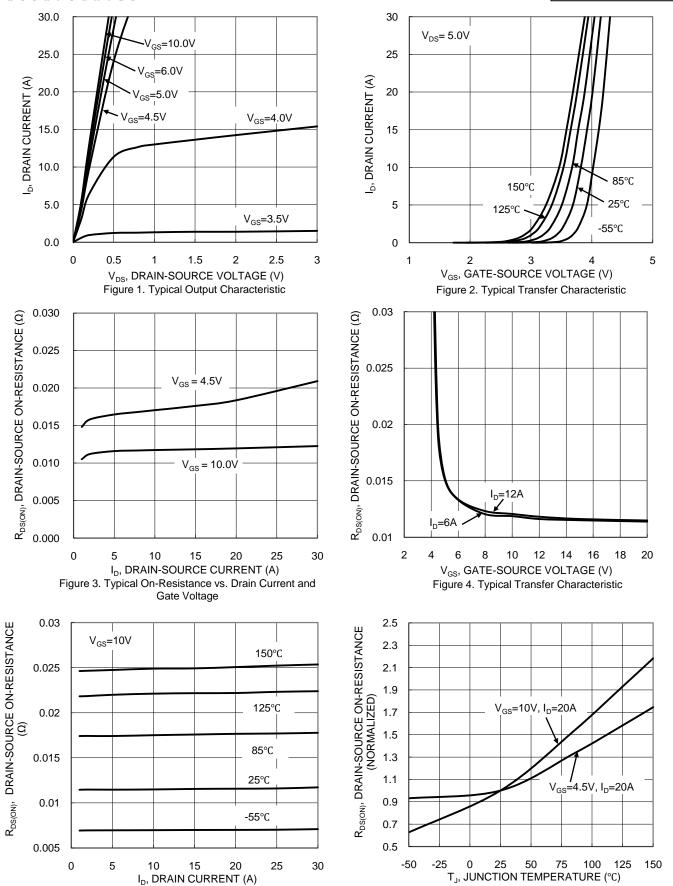


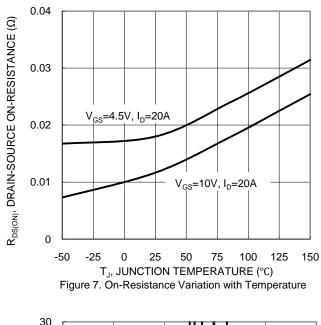
Figure 5. Typical On-Resistance vs Drain Current and

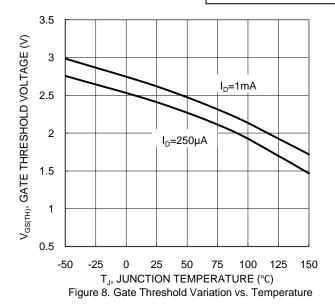
Temperature

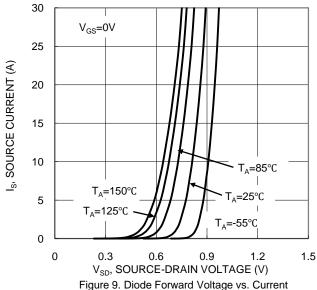
Figure 6. On-Resistance Variation with Temperature

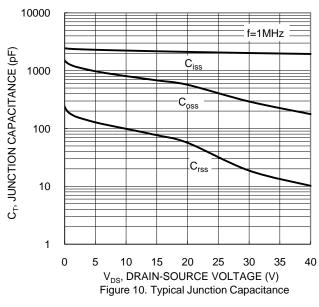


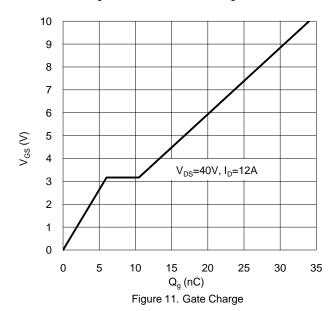












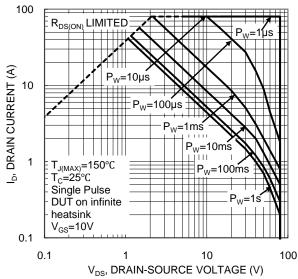
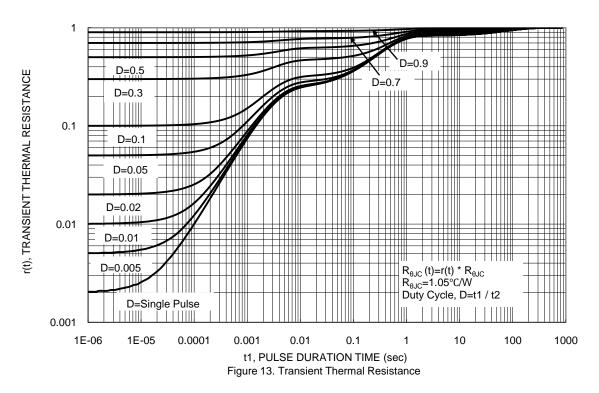


Figure 12. SOA, Safe Operation Area



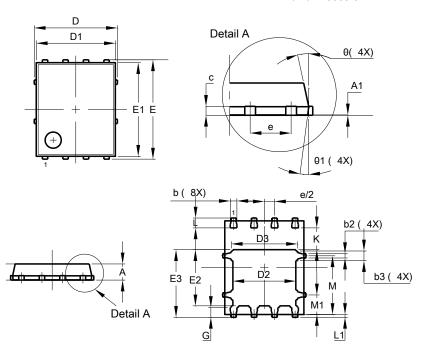




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

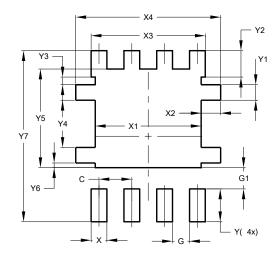


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00				
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	Į	5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70 4.10 3.9				
D3	3.90	4.30	4.10		
Е	•	6.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28 3.68 3.4				
E3	3.99 4.39 4.19				
е	•	1.27 BSC	;		
G	0.51	0.71	0.61		
K	0.51		-		
L	0.51 0.71 0.6		0.61		
L1	0.100 0.200 0.1		0.175		
M			3.635		
M1	1.00	1.40	1.21		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	value (in mm)	
С	1.270	
G	0.660	
G1	0.820	
Х	0.610	
X1	4.100	
X2	0.755	
Х3	4.420	
X4	5.610	
Υ	1.270	
Y1	0.600	
Y2	1.020	
Y3	0.295	
Y4	1.825	
Y5	3.810	
Y6	0.180	
Y7	6.610	



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